BCX19



SEMICONDUCTOR®

BCX19

NPN Medium Power Transistor

- This device is designed for general purpose amplifiers.
- Sourced from process 38.



1. Base 2. Emitter 3. Collector

Absolute Maximum Ratings $T_{C}=25^{\circ}C$ unless otherwise noted

Symbol	Parameter		Value	Units	
V _{CEO}	Collector-Emitter Voltage		45	V	
V _{CBO}	Collector-Base Voltage		50	V	
V _{EBO}	Emitter-Base Voltage		5.0	V	
I _C	Collector current	- Continuous	500	mW	
TJ, Tstg	Junction and Storage Temperature		-55 ~ +150	°C	

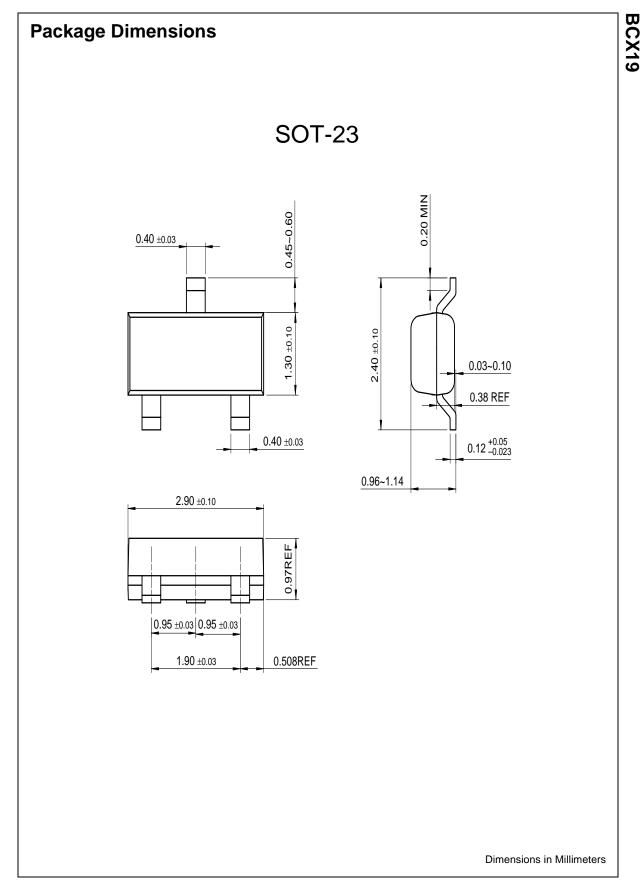
Electrical Characteristics $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
Off Characte	eristics	-				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0$	45			V
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 10 \mu {\rm A}, I_{\rm C} = 0$	50			V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 20V, I_E = 0$ $V_{CB} = 20V, I_E = 0, T_A = 150^{\circ}C$			100 5.0	nA μA
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 5.0V, I_{C} = 0$			10	μΑ
On Characte	eristics			•	•	
h _{FE}	DC Current Gain	$ I_{C} = 100 m A, V_{CE} = 1.0 V \\ I_{C} = 300 m A, V_{CE} = 1.0 V \\ I_{C} = 500 m A, V_{CE} = 1.0 V $	100 70 40		600	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 500 {\rm mA}, I_{\rm B} = 50 {\rm mA}$			0.62	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 500mA, V _{CE} = 1.0V			1.2	V

Thermal Characteristics $T_A=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Max.	Units
PD	Total Device Dissipation	300	mW
	Derate above 25°C	2.4	mW/°C
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient	417	°C/W

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